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NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE15H10A uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

General Features

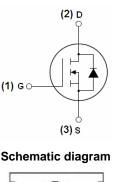
- $V_{DS} = 150V, I_D = 100A$ $R_{DS(ON)} < 11m\Omega @ V_{GS} = 10V$ (Typ:9.5m Ω)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

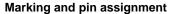
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!









TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE15H10A	NCE15H10A	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_C =25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	150	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	I _D	100	А	
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	70	Α	
Pulsed Drain Current	I _{DM}	390	А	
Maximum Power Dissipation	P _D	370	W	
Derating factor		2.47	W/°C	
Single pulse avalanche energy (Note 5)	Eas	1600	mJ	



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NCE15H10A

Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	℃
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Thermal Characteristic

Thermal Resistance, Junction-to-Cas ^{e(Note 2)}	R _{θJC}	0.41	°C/W
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter Symbol Condition		Min	Тур	Max	Unit	
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	150	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5	3.7	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	9.5	11	mΩ
Forward Transconductance	G FS	V _{DS} =25V,I _D =40A	100	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V -25V/V -0V/	-	7500	-	PF
Output Capacitance	Coss	V_{DS} =25V, V_{GS} =0V, F=1.0MHz	-	640	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVID2	-	426	-	PF
Switching Characteristics (Note 4)	<u>.</u>					
Turn-on Delay Time	t _{d(on)}		-	32.5	-	nS
Turn-on Rise Time	t _r	VDD=75V,ID=2A,RL=15Ω	-	30	-	nS
Turn-Off Delay Time	t _{d(off)}	,RG=2.5Ω,VGS=10V	-	113	-	nS
Turn-Off Fall Time	t _f		-	48	-	nS
Total Gate Charge	Qg	\/ 75\/ L 40A	-	138	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =75V, I_{D} =40A, V_{GS} =10V	-	46	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	39	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =40A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	100	Α
Reverse Recovery Time	t _{rr}	Tj=25℃,I _F =40A,di/dt=100A/μs	-	45		nS
Reverse Recovery Charge	Qrr	(Note3)	-	80		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

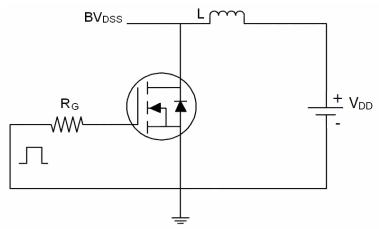
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}\text{C}$,VDD=40V,VG=10V,L=0.5mH,Rg=25 Ω

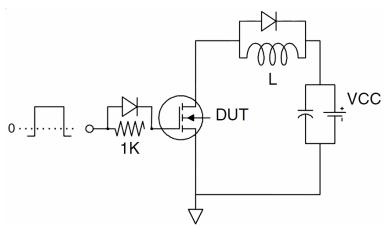


Test circuit

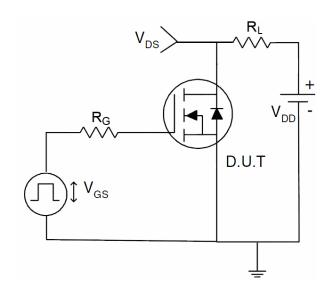
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:





Typical Electrical and Thermal Characteristics (Curves)

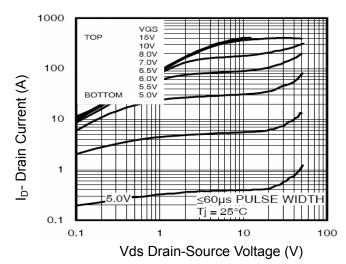


Figure 1 Output Characteristics

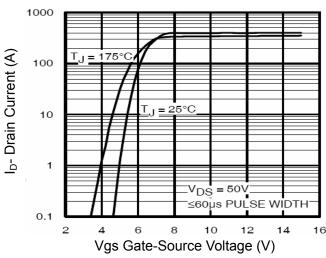


Figure 2 Transfer Characteristics

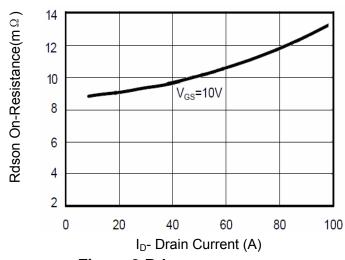


Figure 3 Rdson- Drain Current

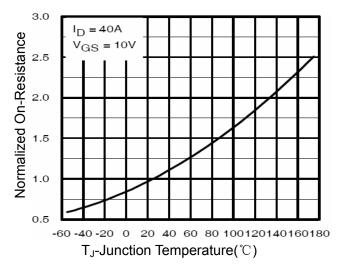


Figure 4 Rdson-JunctionTemperature

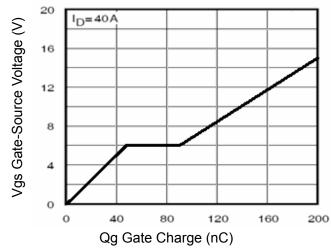


Figure 5 Gate Charge

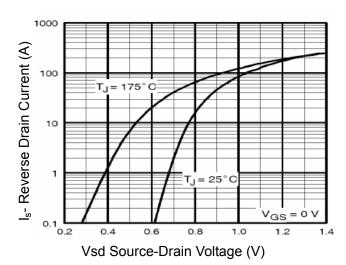


Figure 6 Source- Drain Diode Forward



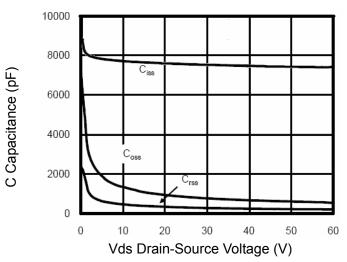


Figure 7 Capacitance vs Vds

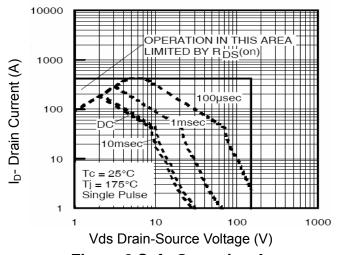


Figure 8 Safe Operation Area

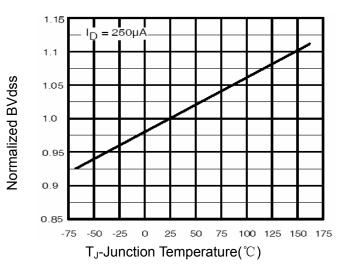


Figure 9 BV_{DSS} vs Junction Temperature

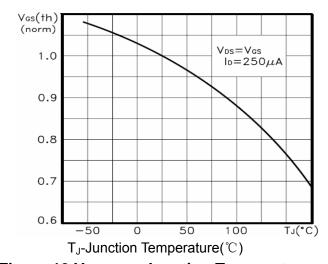


Figure 10 V_{GS(th)} vs Junction Temperature

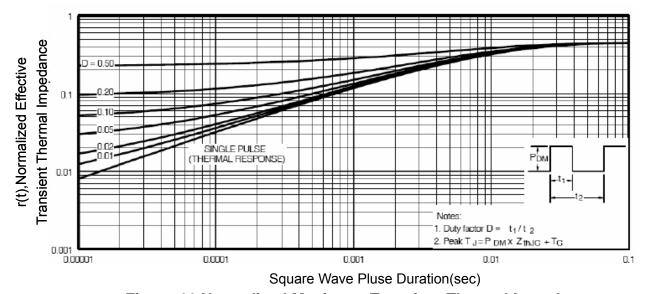
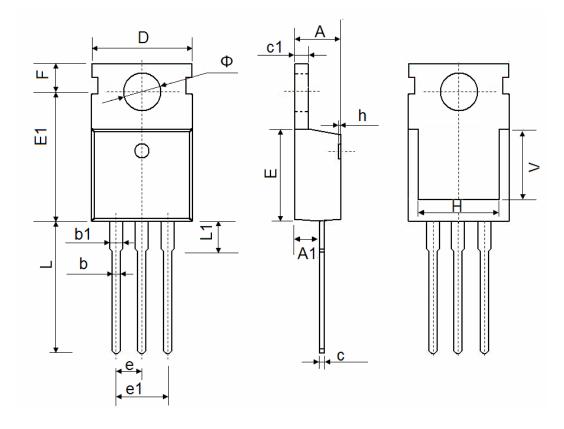


Figure 11 Normalized Maximum Transient Thermal Impedance

Pb Free Product

TO-220-3L Package Information



Symbol	Dimensions I	In Millimeters	Dimensions In Inches			
	Min.	Max.	Min.	Max.		
Α	4.400	4.600	0.173	0.181		
A1	2.250	2.550	0.089	0.100		
b	0.710	0.910	0.028	0.036		
b1	1.170	1.370	0.046	0.054		
С	0.330	0.650	0.013	0.026		
c1	1.200	1.400	0.047	0.055		
D	9.910	10.250	0.390	0.404		
Е	8.9500	9.750	0.352	0.384		
E1	12.650	12.950	0.498	0.510		
е	2.540	TYP.	0.100	00 TYP.		
e1	4.980	5.180	0.196	0.204		
F	2.650	2.950	0.104	0.116		
Н	7.900	8.100	0.311	0.319		
h	0.000	0.300	0.000	0.012		
L	12.900	13.400	0.508	0.528		
L1	2.850	3.250	0.112	0.128		
V	7.500 REF.		0.295 REF.			
Ф	3.400	3.800	0.134	0.150		



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